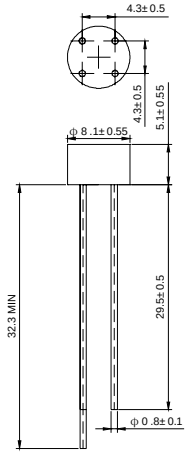
SILICON BRIDGE RECTIFIERS

VOLTAGE RANGE: 50 --- 1000 V
CURRENT: 1.5 A

FEATURES

- ◇ Rating to 1000V PRV
- ◇ Surge overload rating to 30 Amperes peak
- ◇ Ideal for printed circuit board
- ◇ Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- ◇ Lead solderable per MIL-STD-250 method 2026
- ◇ Plastic material has UL flammability recognition 94V-O
- ◇ Weight: 0.050 ounces,1.42 grams
- ◇ Glass passivated chip junctions

WOM



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.
Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		W005	W01	W02	W04	W06	W08	W10	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forw ard Output current @T_C=50℃	$I_{F(AV)}$	1.5							A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load	I_{FSM}	50							A
Maximum instantaneous forw ard voltage at 1.0 A	V_F	1.0							V
Maximum reverse current @T_A=25℃	I_R	5.0							μA
at rated DC blocking voltage @T_A=125℃		0.5							mA
Operating junction temperature range	T_J	- 55 ---- + 125							℃
Storage temperature range	T_{STG}	- 55 ---- + 150							℃

FIG.1 -- PEAK FORWARD SURGE CURRENT

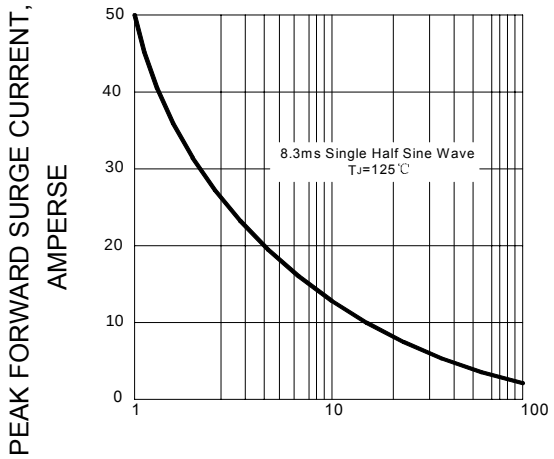


FIG.2 -- FORWARD DERATING CURVE

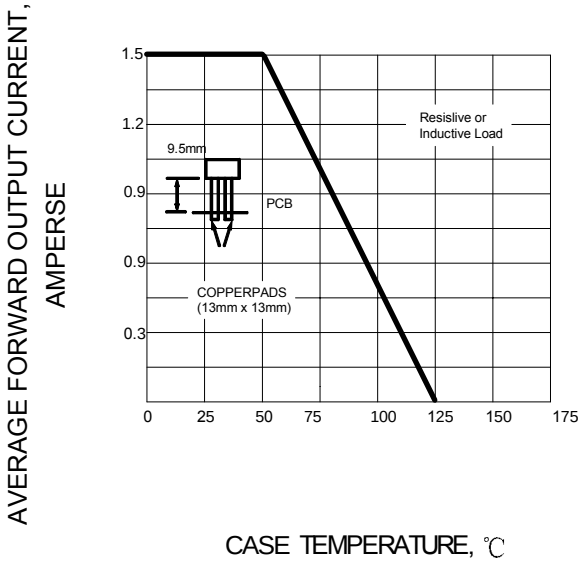


FIG.3 -- TYPICAL FORWARD CHARACTERISTIC

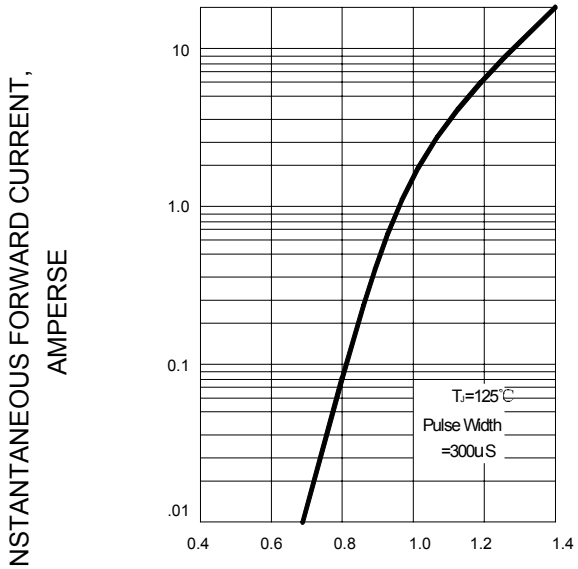


FIG.4 -- TYPICAL REVERSE CHARACTERISTIC

